Regarding the change of names mentioned in the document, such as Mitsubishi Electric and Mitsubishi XX, to Renesas Technology Corp.

The semiconductor operations of Hitachi and Mitsubishi Electric were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.) Accordingly, although Mitsubishi Electric, Mitsubishi Electric Corporation, Mitsubishi Semiconductors, and other Mitsubishi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

Note : Mitsubishi Electric will continue the business operations of high frequency & optical devices and power devices.

Renesas Technology Corp.
Customer Support Dept.
April 1, 2003
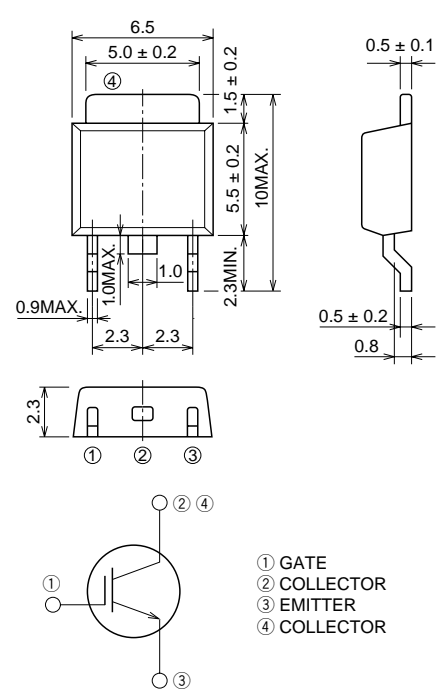
CT20ASL-8

- V_{CES} 400V
- I_{CM} 130A

OUTLINE DRAWING   Dimensions in mm

① GATE
② COLLECTOR
③ EMITTER
④ COLLECTOR

MP-3

APPLICATION

Strobe Flasher.

MAXIMUM RATINGS (Tc = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CES}	Collector-emitter voltage	V_{GE} = 0V	400	V
V_{GES}	Gate-emitter voltage	V_{CE} = 0V, See notice 4	±15	V
V_{GEM}	Peak gate-emitter voltage	V_{CE} = 0V, tw = 10s	±16	V
I_{CM}	Collector current (Pulsed)	See figure 1	130	A
T_j	Junction temperature		−40 ~ +150	°C
T_{stg}	Storage temperature		−40 ~ +150	°C

ELECTRICAL CHARACTERISTICS (Tj = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
$V_{(BR)CES}$	Collector-emitter breakdown voltage	I_C = 1mA, V_{GE} = 0V	450	—	—	V
I_{CES}	Collector-emitter leakage current	V_{CE} = 400V, V_{GE} = 0V	—	—	10	μA
I_{GES}	Gate-emitter leakage current	V_{GE} = ±16V, V_{CE} = 0V	—	—	±0.1	μA
$V_{GE(th)}$	Gate-emitter threshold voltage	V_{CE} = 10V, I_C = 1mA	0.5	—	4.0	V

Feb.1999

PERFORMANCE CURVES

MAXIMUM PULSE COLLECTOR CURRENT

$C_M = 400\mu F$

$T_C \leqq 70°C$

PULSE COLLECTOR CURRENT I_{CM} (A)

GATE-EMITTER VOLTAGE V_{GE} (V)

Figure 1

APPLICATION EXAMPLE

IXe

Vtrig

C_M

V_{CM}

R_G

V_{CE}

V_G

IGBT

TRIGGER SIGNAL   Vtrig

IGBT GATE VOLTAGE V_G

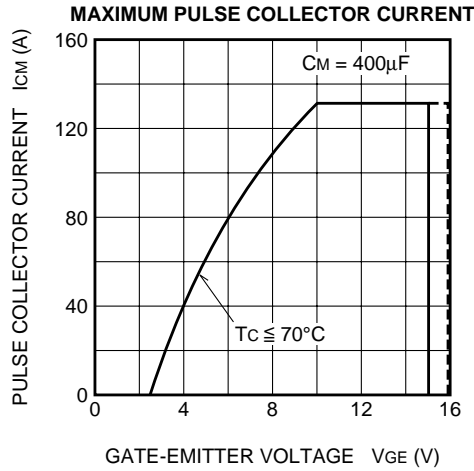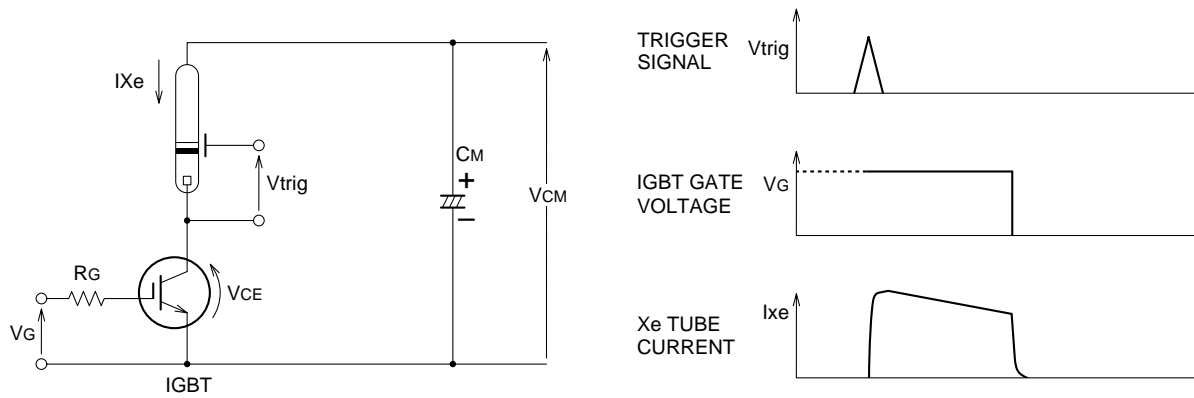Xe TUBE CURRENT   Ixe

RECOMMEND CONDITION   MAXIMUM CONDITION

V_{CM} = 300V   350V
I_P = 120A   130A
C_M = 300μF   400μF
V_{GE} = 12V

Notice 1. Gate drive voltage during on-period must be applied to satisfy the rating of maximum pulse collector current.
And reverse gate current during turn-off must be kept less than 50mA.
(In general, it is satisfied if $R_G \geq 330\Omega$)

Notice 2. IGBT has MOS structure and its gate is insulated by thin silicon oxide.
So please handle carefully not to suffer from electrostatic charge.

Notice 3. The operation life should be endured 5,000 shots under the charge current
($I_{xe} \leq 130A$: full luminescence condition) of main condenser (C_M=400μF).
Repetition period under full luminescence condition is over 3 seconds.

Notice 4. Total operation hours must be applied within 5,000 hours.